**Index**

|  |  |  |
| --- | --- | --- |
| Experiment No. | Name of the Experiment | Page No. |
| 01 | To study the characteristics of diode that act as a switch. |  |
| 02 | To study the characteristics of diode AND gate. |  |
| 03 | To study the characteristics of diode OR gate. |  |
| 04 | To study the characteristics of transistor AND gate. |  |
| 05 | To study the characteristics of transistor OR gate. |  |
| 06 | To study the characteristics of 2-input RTL NOR gate. |  |
| 07 | To study the characteristics of DTL NAND gate. |  |
| 08 | To study the characteristics of 3-input TTL NAND gate. |  |
| 09 | To study the characteristics of 2-input TTL NAND gate with totem pole. |  |
| 10 | To study the characteristics of TTL NOR gate with totem pole. |  |
| 11 | To study the characteristics of astable multivibrator using 555 timer IC. |  |
| 12 | To study the characteristics of R/2R ladder network. |  |